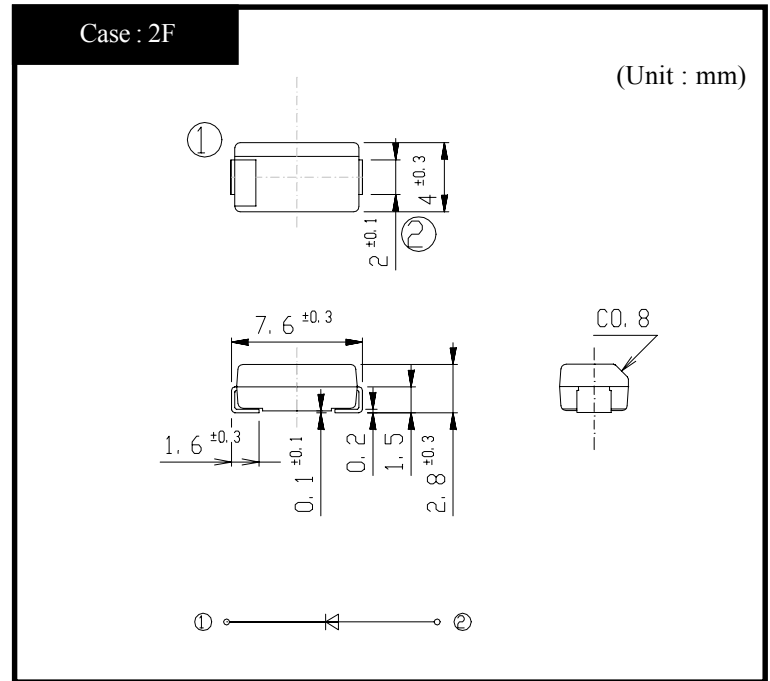


KP4N12

OUTLINE DIMENSIONS



RATINGS

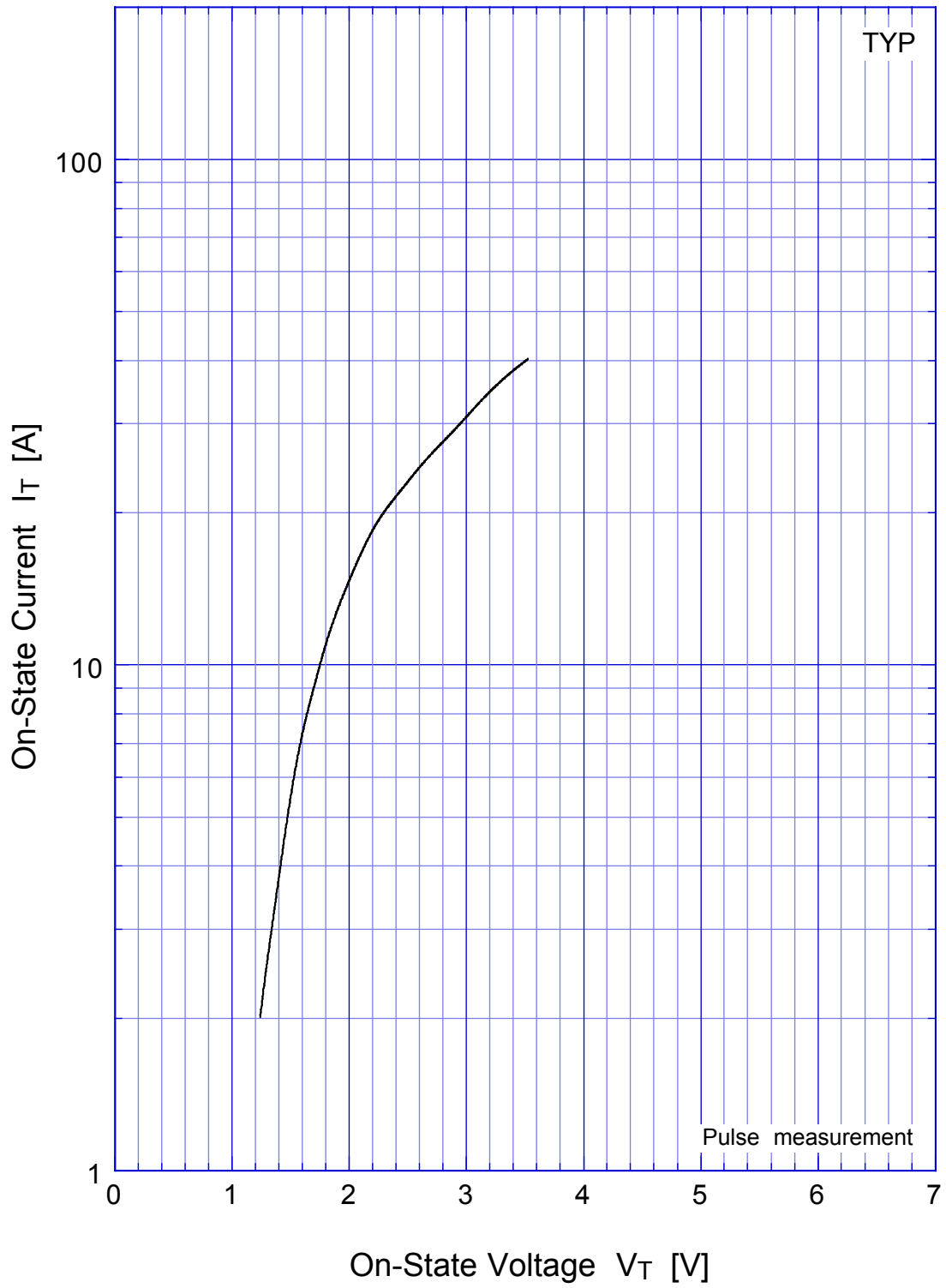
● Absolute Maximum Ratings

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T _{stg}		-40~125	°C
Junction Temperature	T _j		125	°C
Maximum Off-State Voltage	V _{DRM}		100	V
Surge On-State Current	I _{TSM}	10/1000 μs, Non-repetitive	40	A
		10/200 μs, Non-repetitive	60	
		8/20 μs, Non-repetitive	150	

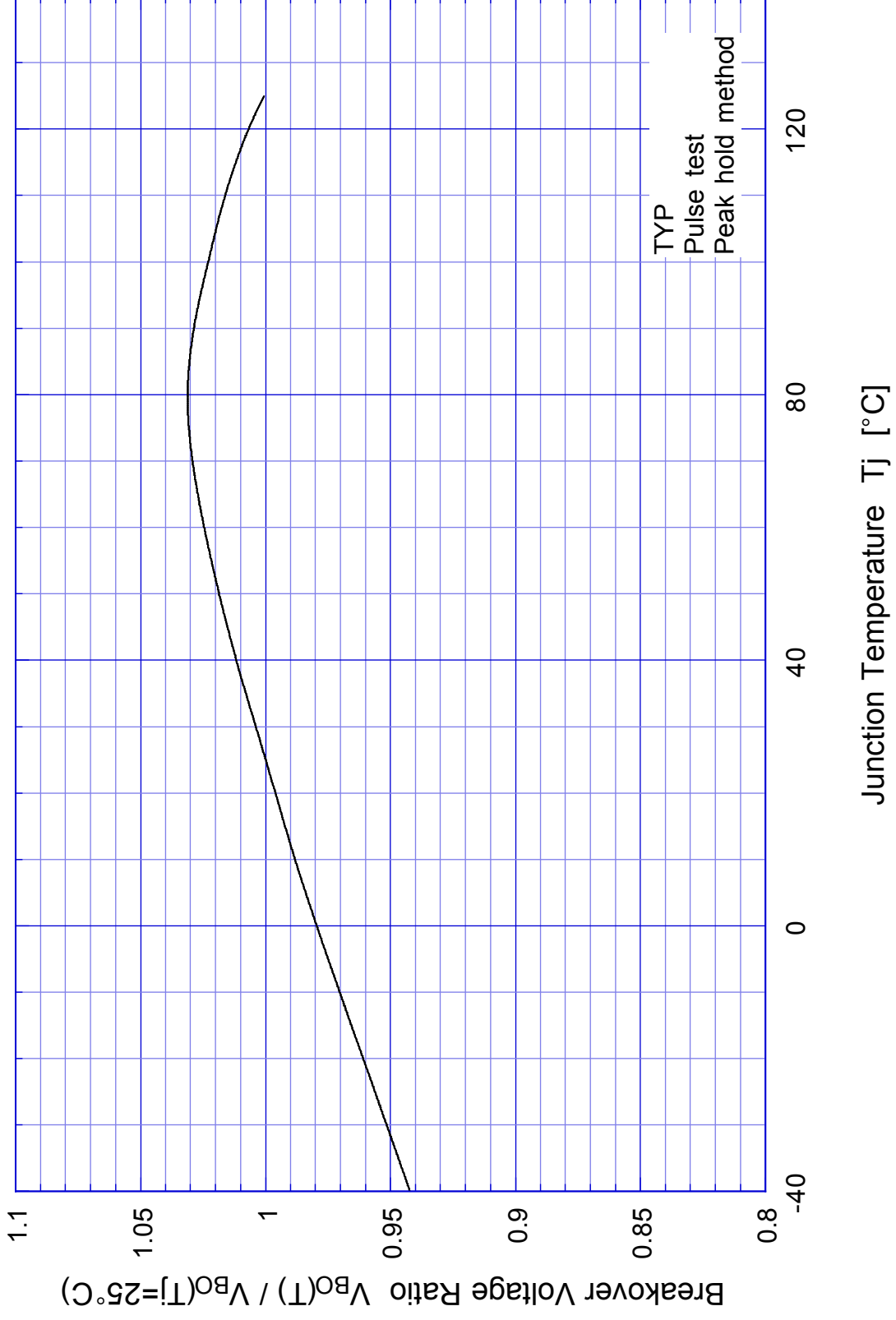
● Electrical Characteristics (Tl=25°C)

Item	Symbol	Conditions	Ratings	Unit
Breakover Voltage	V _{BO}	Pulse measurement (Peak hold)	Min 110	V
Off-State Current	I _{DRM}	V _D = V _{DRM}	Max 10	μA
Holding Current	I _H	Pulse measurement	Min 100	mA
On-State Voltage	V _T	I _T = 2A	TYP 1.25	V
Junction Capacitance	C _j	f = 1kHz OSC = 1V, V _D = 50V	Max 50	pF
Clamping Voltage	V _{CL}	dv/dt = 100V/μs	Max 135	V

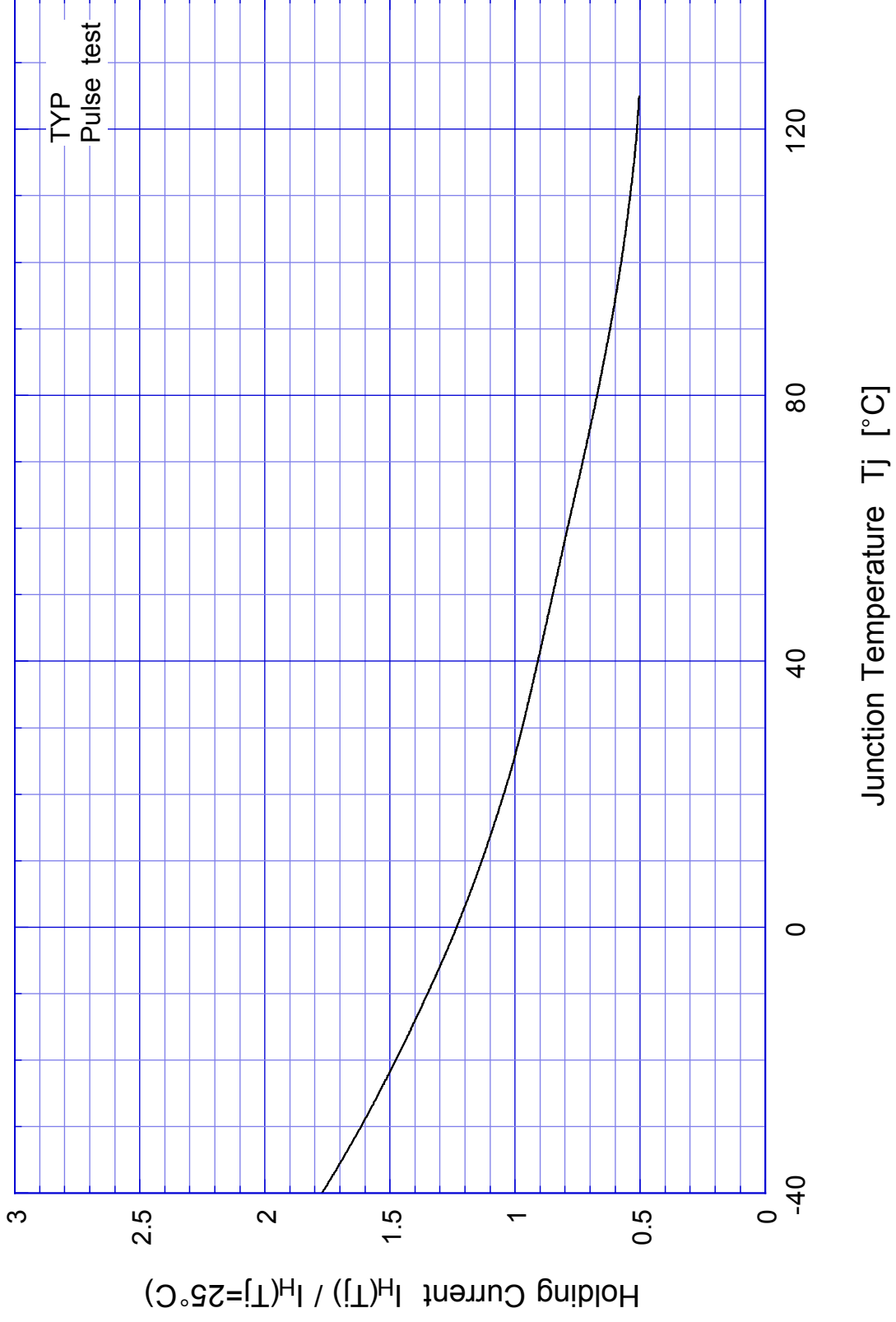
KP4N12 On-State Voltage - On-State Current



KP4N12 Breakover Voltage - Junction Temperature

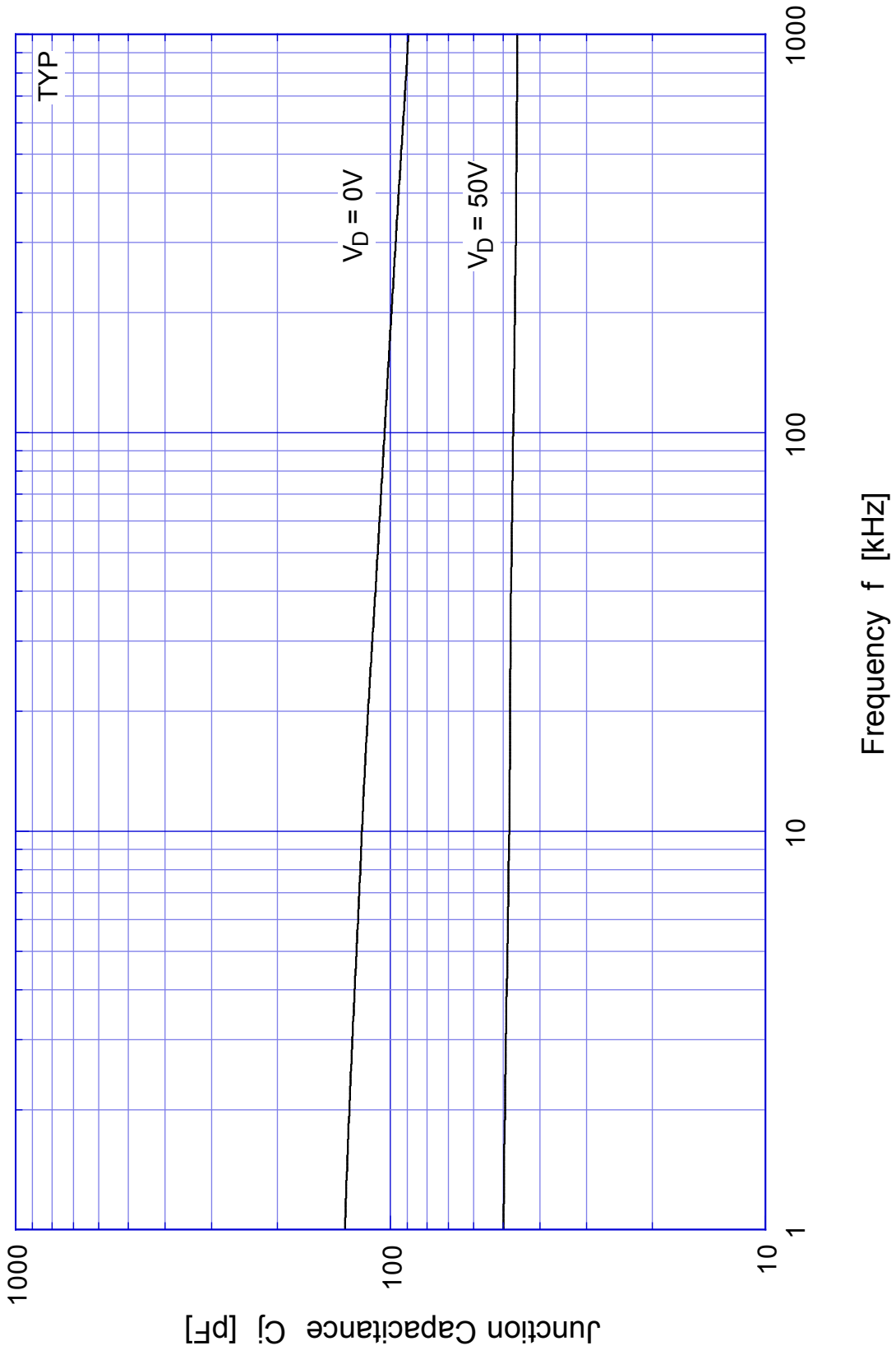


KP4N12 Holding Current - Junction Temperature

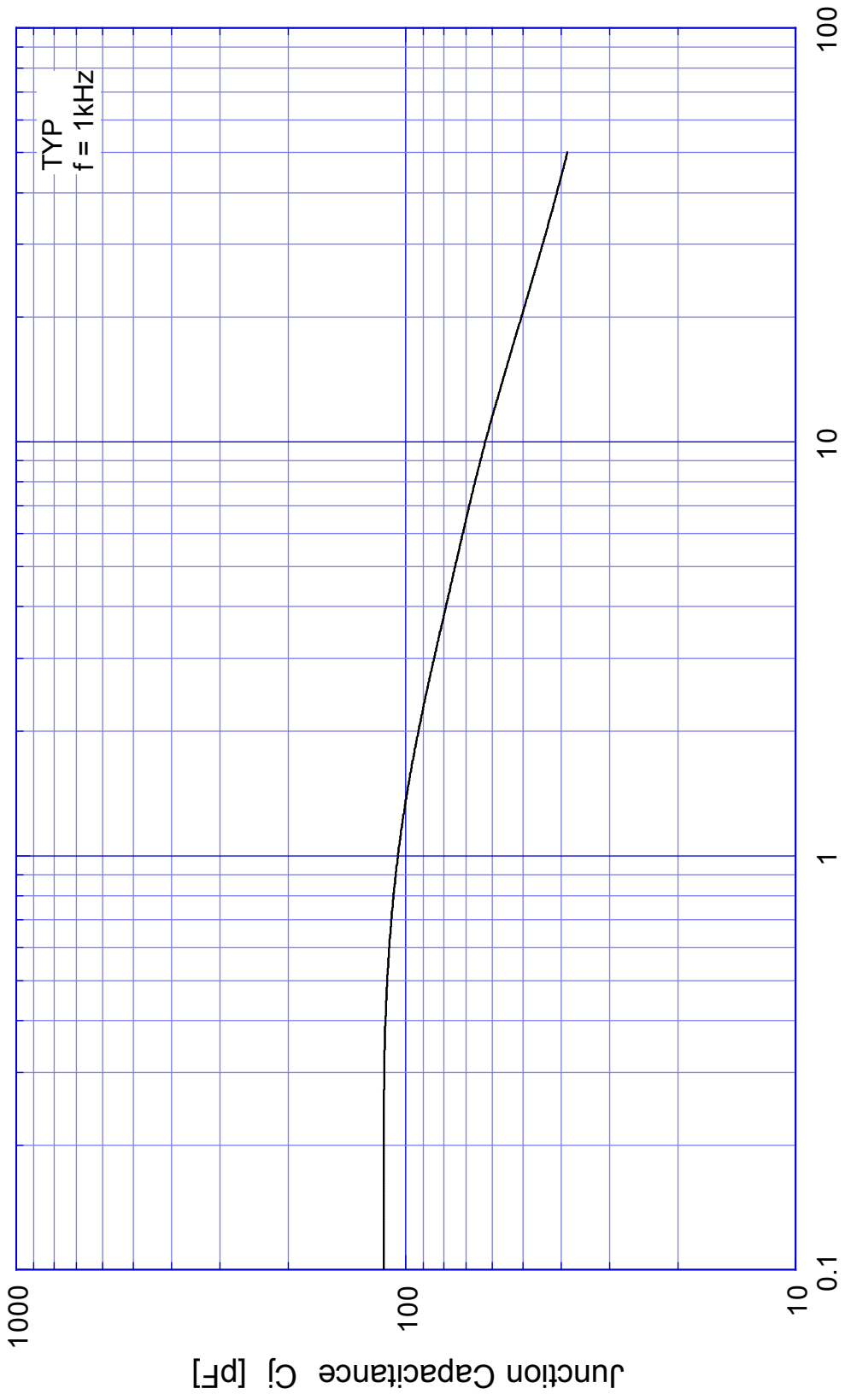


KP4N12

Junction Capacitance



KP4N12 Junction Capacitance



Off-State Applied Voltage V_D [V]